Part Number Customer						
Category	Parameter		Specification	Measurement Method		
OverallWafer	1.0 Diameter		150.00 +/- 0.30 mm			
	2.0	Primary Flat Orientation	{110}+/-1 degree	Wafer Vendor		
	3.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor		
	4.0	Secondary Flat Orientation	None			
	5.0	Overall Thickness	681.00 +/- 6.00 μm	ADE, 100%		
	6.0	Total Thickness Variation (TTV)	<5.00µm	Guaranteed by Process		
	7.0	Bow	<80.00µm	ADE to ASTM F534, 20%		
	8.0	Warp	<80.00µm	ADE to ASTM F657, 20%		
	10.0	Edge Exclusion	7mm			
HandleSilicon	11.0	Handle Growth Method	CZ	Wafer Vendor		
	12.0	Handle Orientation	{100} +/- 1 degree	Wafer Vendor		
	13.0	Handle Thickness	600.00 +/- 5.00 μm	ADE, 100%		
	14.0	Handle Doping Type	Ν	Wafer Vendor		
	15.0	Handle Dopant	Phosphorous	Wafer Vendor		
	16.0	Handle Resistivity	1 - 10 Ohmcm	Wafer Vendor		
	17.0	Backside Finish	Lapped and Etched	Wafer Vendor		
BuriedOxide	18.0	Oxide Type	Thermal			
	19.0	Oxide Thickness	20,000.00 +/- 1,000.00 A	Nanospec centre point, 4%		
	20.0	Oxide formed on	Device Wafer			
DeviceSilicon	21.0	Device Growth Method	Low Oi CZ	Wafer Vendor		
	22.0	Oxygen Concentration	<13.40ppma	New ASTM		
	23.0	Device Orientation	{100} +/- 1 degree	Wafer Vendor		
	24.0	Nominal Thickness	73.00 +/- 1.00 μm	FTIR, 100% 9-Pt (note3)		
	25.0	Distance to device silicon edge from wafer edge	< 5mm	Typical by Process, no edge grind.		
	26.0	Device Doping Type	Ν	Wafer Vendor		
	27.0	Device Dopant	Phosphorous	Wafer Vendor		
	28.0	Device Resistivity	1 - 3 Ohm-cm	Wafer Vendor		
	32.0	Voids	0	Bright Light, 100% (note2)		
	33.0	Scratches	<25mm total length	Bright Light, 100% (note2)		
	34.0	Haze	none	Bright Light, 100% (note2)		

Icemos Technology Ltd

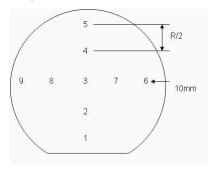
**Product Specification** 

1900.390002

Part Number		Customer		
Category	Parameter	Specification	Measurement Method	
Shipping Details	g Details Wafer per box : Max 25			
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging		
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness		
Explanatory Notes	1. Microscope inspection performed using microscope scan as below. 5x objective.			

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information